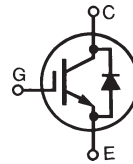


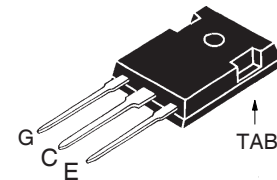
Medium speed low V_{sat} PT
IGBT for 5-40kHz switching



$$V_{CES} = 600V$$

$$I_{C110} = 36A$$

$$V_{CE(sat)} \leq 1.8V$$

TO-247 AD (IXGH)


G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C110}	$T_C = 110^\circ\text{C}$	36	A
I_{F110}	$T_C = 110^\circ\text{C}$	10	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	200	A
SSOA	$V_{GE} = 15V, T_J = 125^\circ\text{C}, R_G = 5\Omega$	$I_{CM} = 80$	A
(RBSOA)	Clamped inductive load @ $V_{CE} \leq 600V$		
P_C	$T_C = 25^\circ\text{C}$	250	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
T_L	Maximum lead temperature for soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062 in.) from case for 10s	260	$^\circ\text{C}$
Weight		6	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = V_{CES}$			75 μA
	$V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			500 μA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 30A, V_{GE} = 15V, \text{Note 1}$	1.5	1.8	V

Features

- Optimized for low conduction and switching losses
- Square RBSOA
- Anti-parallel ultra fast diode
- International standard package

Advantages

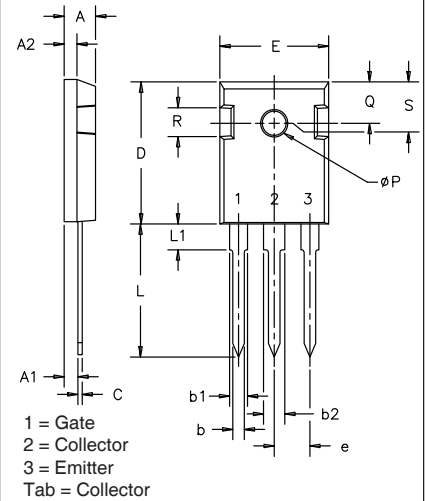
- High power density
- Low gate drive requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 30\text{A}, V_{CE} = 10\text{V}$, Note 1	28	42	S
C_{ies} C_{oes} C_{res}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2280	pF
			120	pF
			32	pF
Q_g Q_{ge} Q_{gc}	$I_C = 30\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		80	nC
			12	nC
			36	nC
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$		19	ns
			24	ns
			0.54	mJ
			125	200 ns
			100	160 ns
			0.80	1.5 mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$		19	ns
			26	ns
			0.90	mJ
			180	ns
			170	ns
			1.50	mJ
R_{thJC} R_{thCK}		0.21	0.50 °C/W °C/W	

TO-247 (IXGH) AD Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A1	.087	.102	2.2	2.54
A2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b1	.065	.084	1.65	2.13
b2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
øP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

Reverse Diode (FRED)

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 10\text{A}, V_{GE} = 0\text{V}$, Note 1 $T_J = 150^\circ\text{C}$		1.7	3.0 V V
t_{rr} I_{RM}	$I_F = 10\text{A}, -di_F/dt = 200\text{A}/\mu\text{s}$ $V_R = 300\text{V}$ $T_J = 100^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 100^\circ\text{C}$		60	ns
				3 4
R_{thJC}				2.5 °C/W

Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

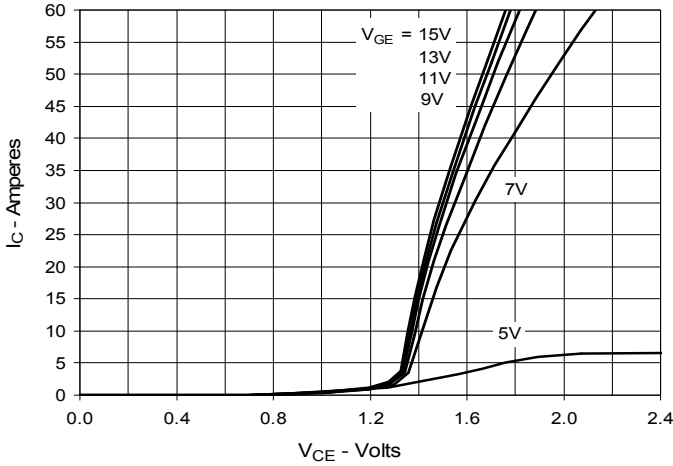
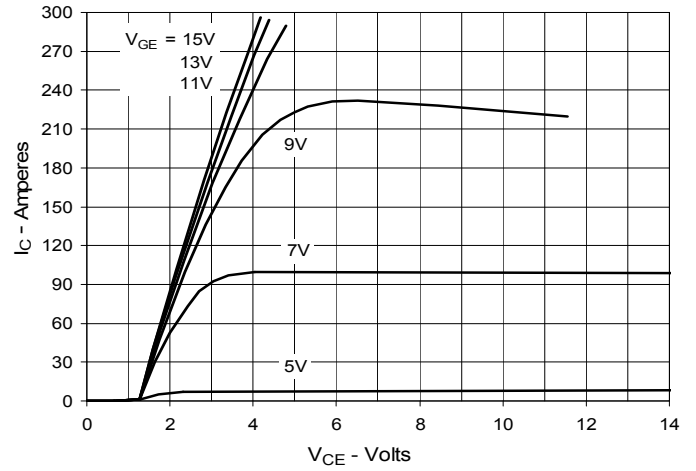
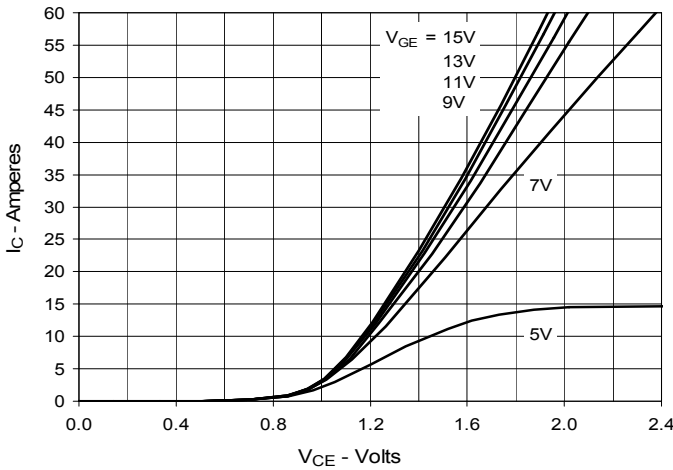
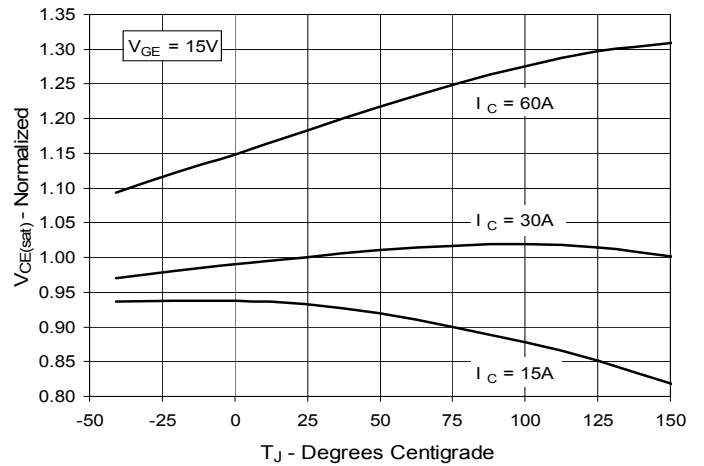
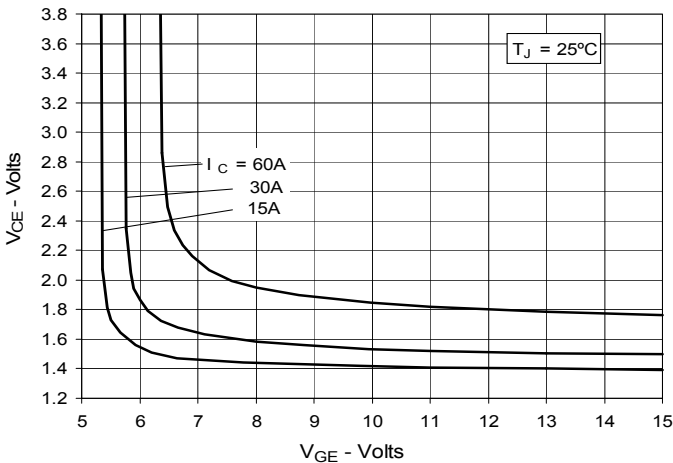
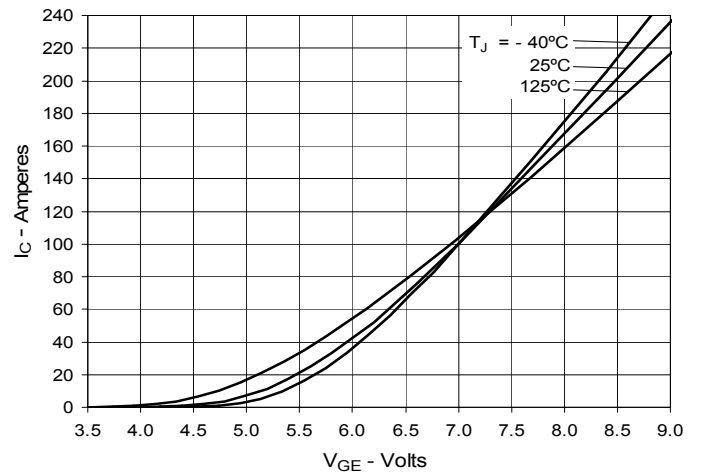
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. Dependence of $V_{CE(sat)}$ on
Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter Voltage**

Fig. 6. Input Admittance


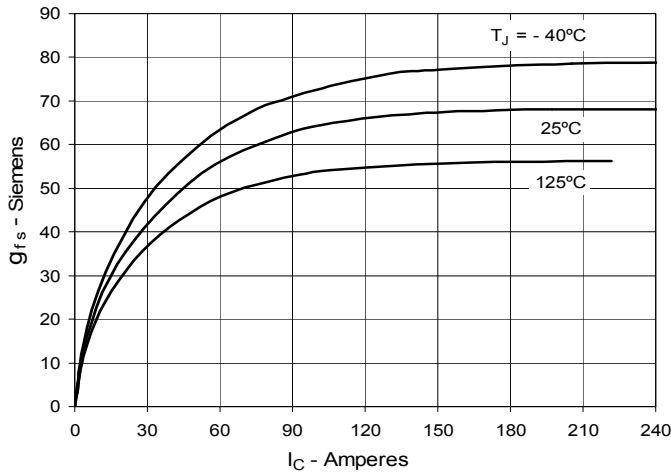
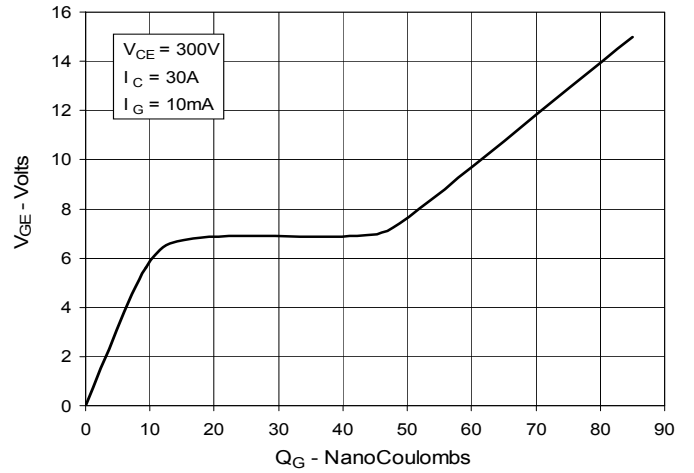
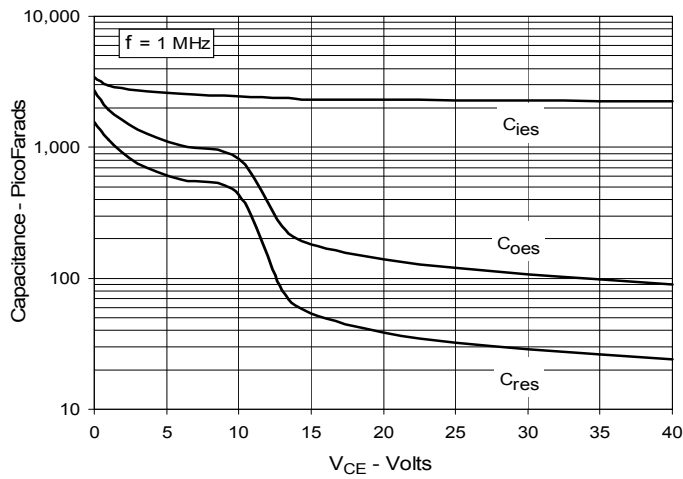
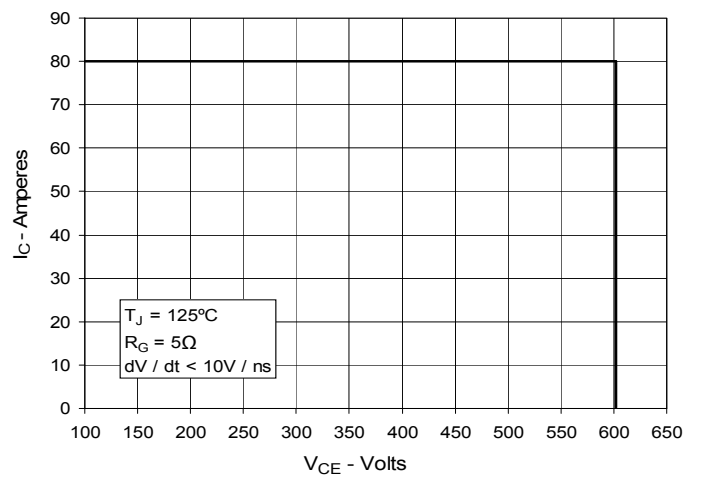
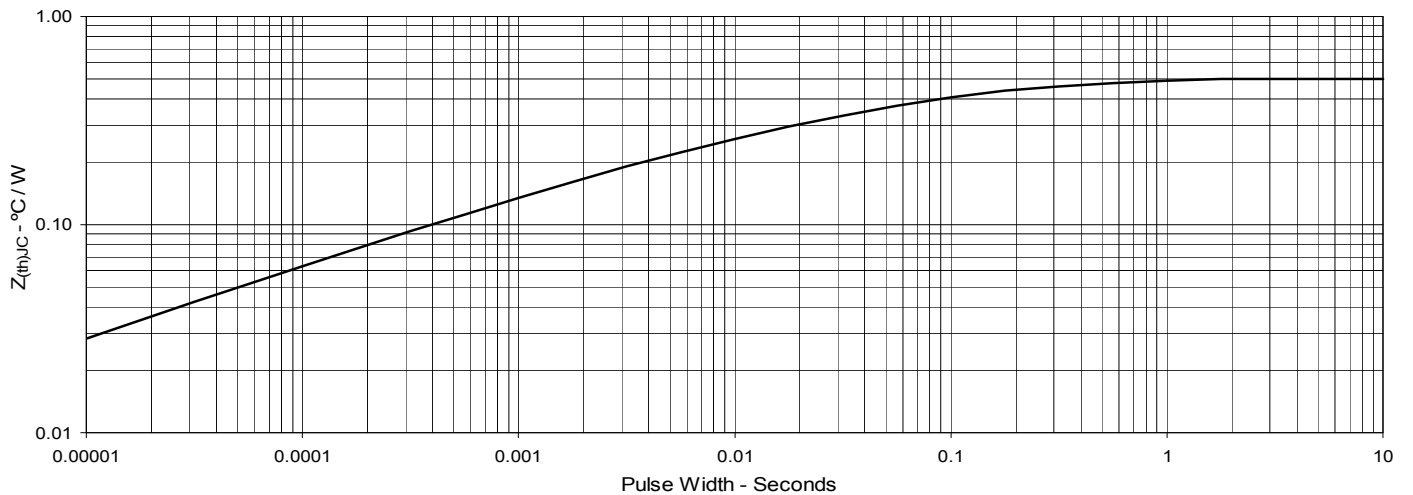
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


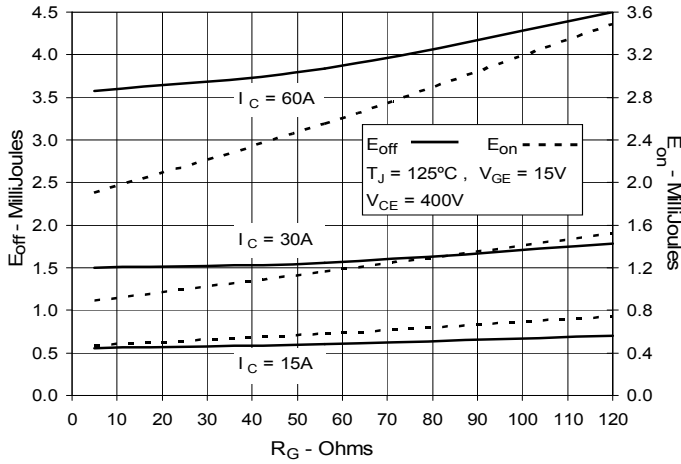
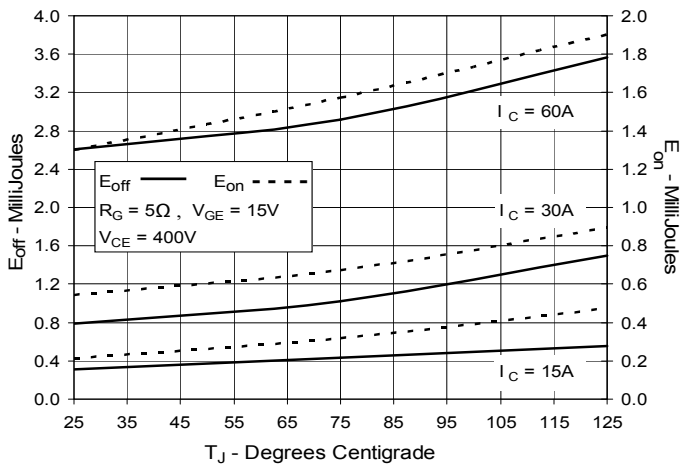
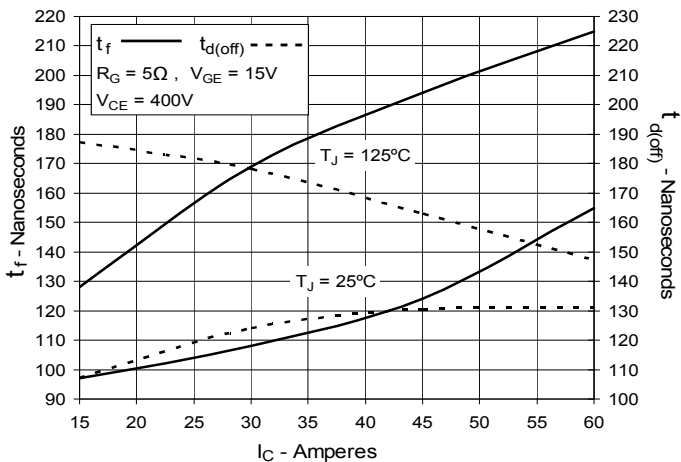
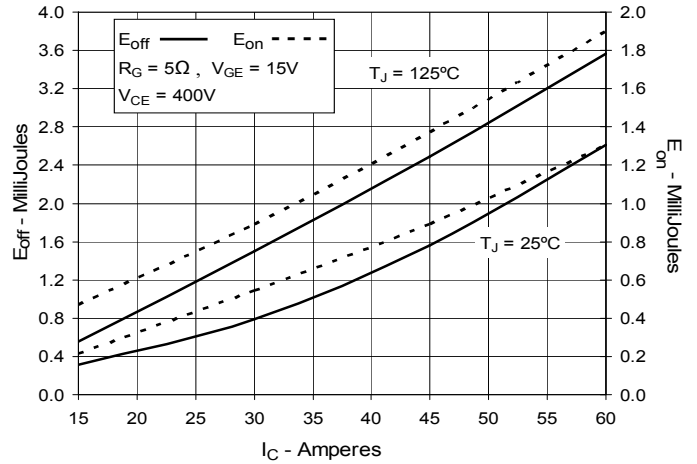
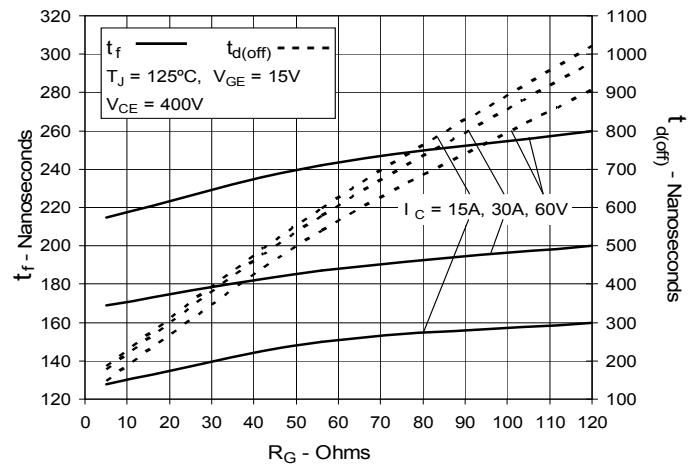
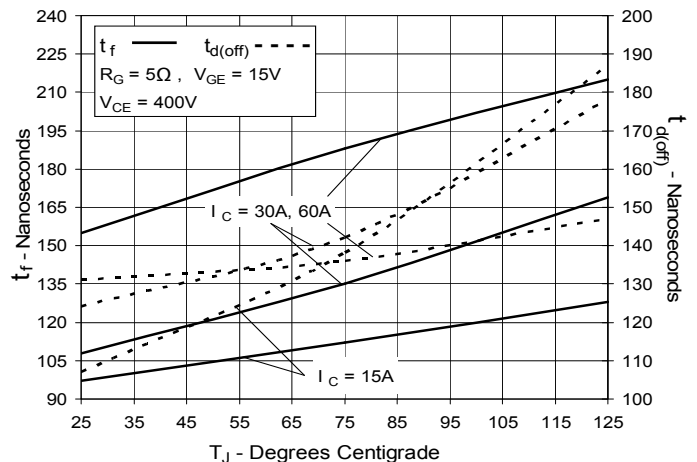
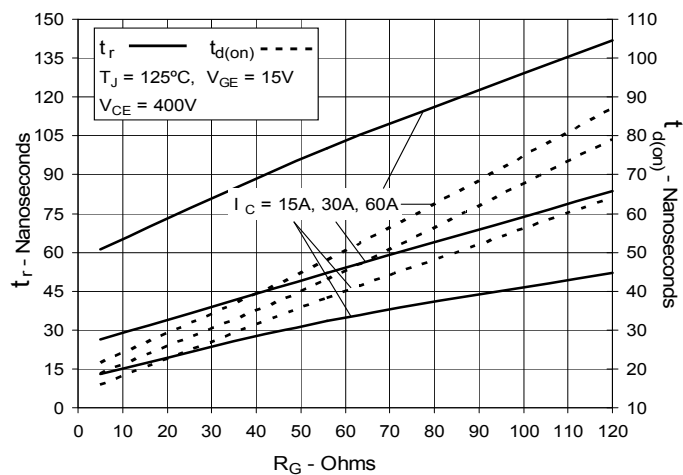
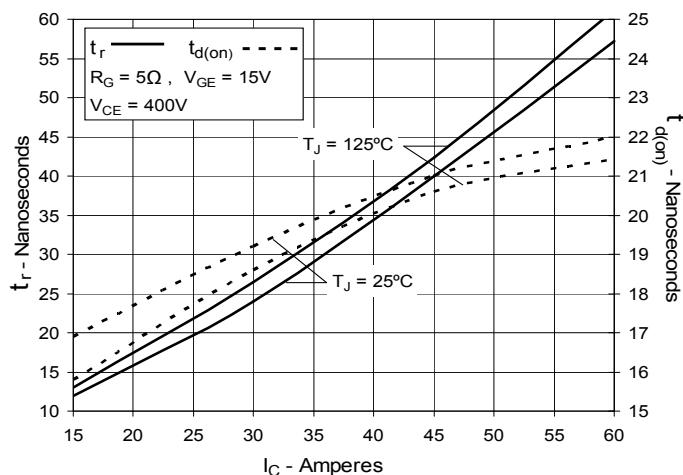
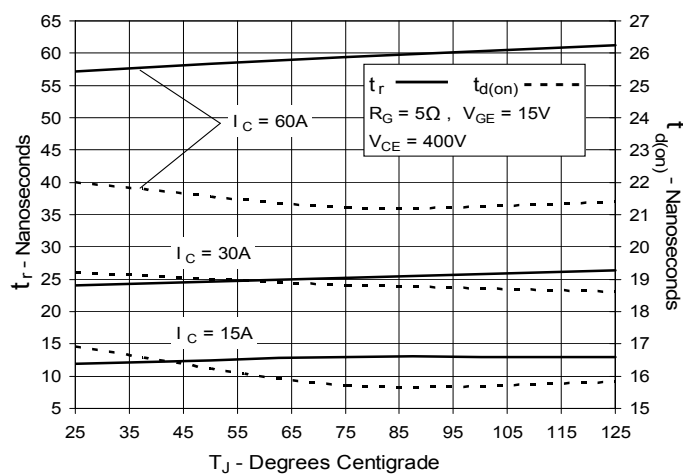
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature


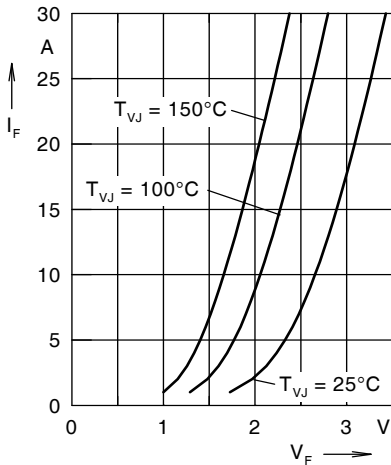


Fig. 21. Forward current I_F versus V_F

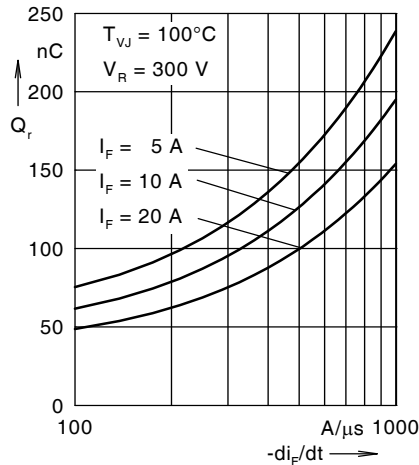


Fig. 22. Reverse recovery charge Q_r

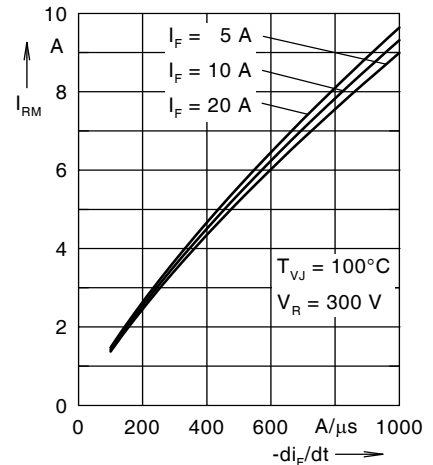


Fig. 23. Peak reverse current I_{RM}

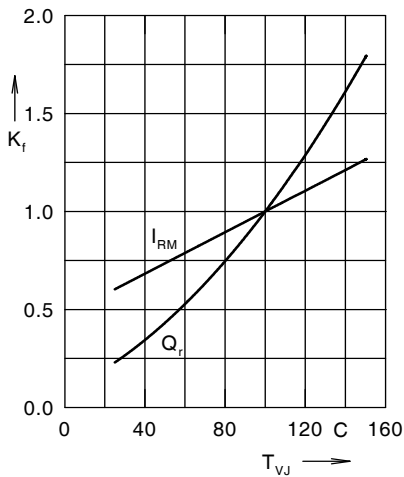


Fig. 24. Dynamic parameters Q_r , I_{RM}

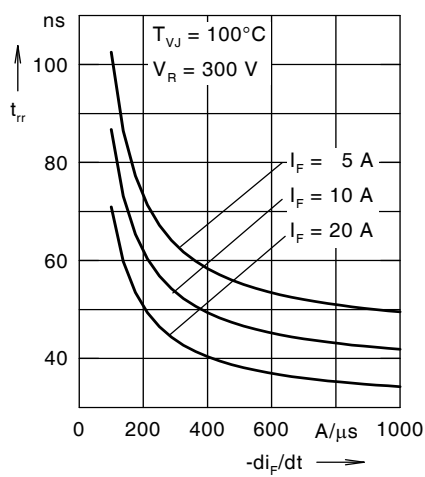


Fig. 25. Recovery time t_{rr} versus $-di_F/dt$

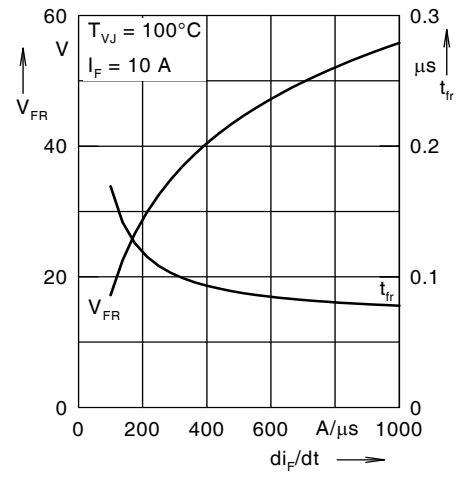


Fig. 26. Peak forward voltage V_{FR} and t_{rr}

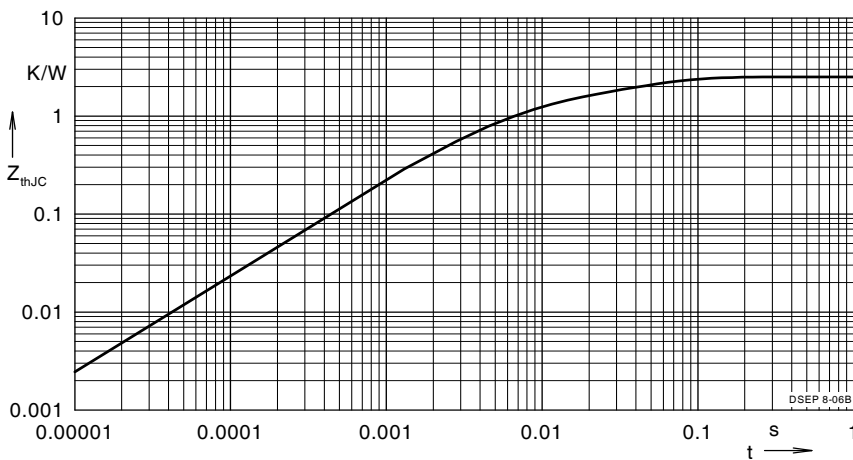


Fig. 27. Transient thermal resistance junction-to-case

NOTE: Fig. 2 to Fig. 6 shows typical values

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	1.449	0.0052
2	0.5578	0.0003